

# EVLYS LTD. - POWER SEMICONDUCTORS DEVICES - Wholesale and Retail.

## Phase Control Disc Thyristor Type DT70-2000-18

High power cycling capability / Low on-state and switching losses  
Designed for traction and industrial applications

Mean on-state current	$I_{TAV}$		2000 A		
Repetitive peak off-state voltage	$V_{DRM}$		1000 ÷ 1800 V		
Repetitive peak reverse voltage	$V_{RRM}$				
Turn-off time	$t_q$		250 $\mu$ s		
$V_{DRM}, V_{RRM}, V$	1000	1200	1400	1600	1800
Voltage code	10	12	14	16	18
$T_j, ^\circ C$	- 60 ÷ 125				

### MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions	
<b>ON-STATE</b>					
$I_{TAV}$	Mean on-state current	A	2000 2515 3114	$T_c = 96^\circ C$ , Double side cooled $T_c = 85^\circ C$ , Double side cooled $T_c = 70^\circ C$ , Double side cooled 180° half-sine wave; 50 Hz	
$I_{TRMS}$	RMS on-state current	A	3140	$T_c = 96^\circ C$ , Double side cooled 180° half-sine wave; 50 Hz	
$I_{TSM}$	Surge on-state current	kA	44.0 51.0	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; 50 Hz ( $t_p = 10$ ms); single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ $\mu$ s; $di_G/dt \geq 1$ A/ $\mu$ s
			47.0 54.0	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; 60 Hz ( $t_p = 8.3$ ms); single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ $\mu$ s; $di_G/dt \geq 1$ A/ $\mu$ s
$I^2t$	Safety factor	$A^2s \cdot 10^3$	9680 13005	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; 50 Hz ( $t_p = 10$ ms); single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ $\mu$ s; $di_G/dt \geq 1$ A/ $\mu$ s
			9165 12100	$T_j = T_{jmax}$ $T_j = 25^\circ C$	180° half-sine wave; 60 Hz ( $t_p = 8.3$ ms); single pulse; $V_D = V_R = 0$ V; Gate pulse: $I_G = 2$ A; $t_{GP} = 50$ $\mu$ s; $di_G/dt \geq 1$ A/ $\mu$ s
<b>BLOCKING</b>					
$V_{DRM}, V_{RRM}$	Repetitive peak off-state and Repetitive peak reverse voltages	V	1000÷1800	$T_{jmin} < T_j < T_{jmax}$ ; 180° half-sine wave; 50 Hz; Gate open	
$V_{DSM}, V_{RSM}$	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	1100÷1900	$T_{jmin} < T_j < T_{jmax}$ ; 180° half-sine wave; 50 Hz; single pulse; Gate open	
$V_D, V_R$	Direct off-state and Direct reverse voltages	V	0.75· $V_{DRM}$ 0.75· $V_{RRM}$	$T_j = T_{jmax}$ ; Gate open	

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<b>TRIGGERING</b>				
$I_{FGM}$	Peak forward gate current	A	8	$T_j = T_{j\ max}$
$V_{RGM}$	Peak reverse gate voltage	V	5	
$P_G$	Gate power dissipation	W	5	$T_j = T_{j\ max}$ for DC gate current
<b>SWITCHING</b>				
$(di_T/dt)_{crit}$	Critical rate of rise of on-state current non-repetitive (f=1 Hz)	A/ $\mu$ s	630	$T_j = T_{j\ max}; V_D = 0.67 \cdot V_{DRM}; I_{TM} = 2 I_{TAV};$ Gate pulse: $I_G = 2\ A;$ $t_{GP} = 50\ \mu s; di_G/dt \geq 1\ A/\mu s$
<b>THERMAL</b>				
$T_{stg}$	Storage temperature	$^{\circ}C$	-60 ÷ 125	
$T_j$	Operating junction temperature	$^{\circ}C$	-60 ÷ 125	
<b>MECHANICAL</b>				
F	Mounting force	kN	33.0 ÷ 40.0	
a	Acceleration	$m/s^2$	50 100	Device unclamped Device clamped

## CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
<b>ON-STATE</b>					
$V_{TM}$	Peak on-state voltage, max	V	1.45	$T_j = 25\ ^{\circ}C; I_{TM} = 5000\ A$	
$V_{T(TO)}$	On-state threshold voltage, max	V	0.85	$T_j = T_{j\ max};$ $0.5 \pi I_{TAV} < I_T < 1.5 \pi I_{TAV}$	
$r_T$	On-state slope resistance, max	$m\Omega$	0.120		
$I_L$	Latching current, max	mA	1500	$T_j = 25\ ^{\circ}C; V_D = 12\ V;$ Gate pulse: $I_G = 2\ A;$ $t_{GP} = 50\ \mu s; di_G/dt \geq 1\ A/\mu s$	
$I_H$	Holding current, max	mA	300	$T_j = 25\ ^{\circ}C;$ $V_D = 12\ V; \text{Gate open}$	
<b>BLOCKING</b>					
$I_{DRM}, I_{RRM}$	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	200	$T_j = T_{j\ max};$ $V_D = V_{DRM}; V_R = V_{RRM}$	
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage <sup>1)</sup> , min	V/ $\mu$ s	1000	$T_j = T_{j\ max};$ $V_D = 0.67 \cdot V_{DRM}; \text{Gate open}$	
<b>TRIGGERING</b>					
$V_{GT}$	Gate trigger direct voltage, max	V	5.00	$T_j = T_{j\ min}$ $T_j = 25\ ^{\circ}C$ $T_j = T_{j\ max}$	$V_D = 12\ V; I_D = 3\ A;$ Direct gate current
			3.00		
$I_{GT}$	Gate trigger direct current, max	mA	500	$T_j = T_{j\ min}$ $T_j = 25\ ^{\circ}C$ $T_j = T_{j\ max}$	
			300		
$V_{GD}$	Gate non-trigger direct voltage, min	V	0.35	$T_j = T_{j\ max};$ $V_D = 0.67 \cdot V_{DRM};$ Direct gate current	
$I_{GD}$	Gate non-trigger direct current, min	mA	15.00		
<b>SWITCHING</b>					
$t_{gd}$	Delay time	$\mu$ s	4.00	$T_j = 25\ ^{\circ}C; V_D = 0.4 \cdot V_{DRM}; I_{TM} = I_{TAV};$ Gate pulse: $I_G = 2\ A;$ $t_{GP} = 50\ \mu s; di_G/dt \geq 1\ A/\mu s$	
$t_q$	Turn-off time <sup>2)</sup> , max	$\mu$ s	250	$dv_D/dt = 50\ V/\mu s; T_j = T_{j\ max}; I_{TM} = 2000\ A;$ $di_R/dt = -10\ A/\mu s; V_R = 100\ V;$ $V_D = 0.67 V_{DRM};$	
$Q_{rr}$	Total recovered charge, max	$\mu$ C	4000	$T_j = T_{j\ max}; I_{TM} = 2000\ A;$ $di_R/dt = -10\ A/\mu s;$ $V_R = 100\ V$	
$t_{rr}$	Reverse recovery time, max	$\mu$ s	33		
$I_{rrM}$	Peak reverse recovery current, max	A	242		

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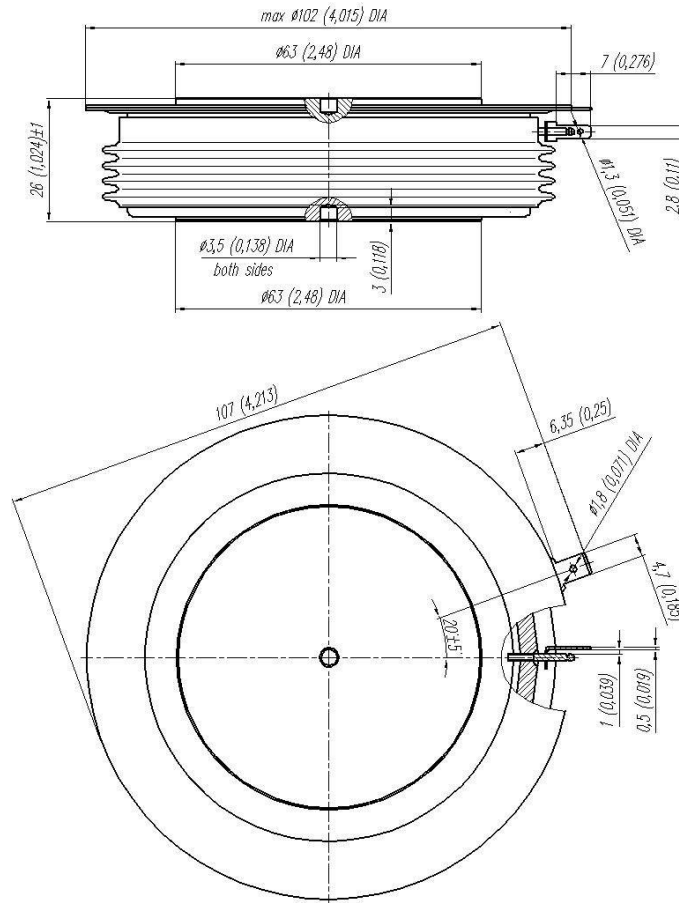
<b>THERMAL</b>					
R <sub>thjc</sub>	Thermal resistance, junction to case, max	°C/W	0.0100	Direct current	Double side cooled
R <sub>thjc-A</sub>			0.0220		Anode side cooled
R <sub>thjc-K</sub>			0.0180		Cathode side cooled
R <sub>thck</sub>	Thermal resistance, case to heatsink, max	°C/W	0.0030	Direct current	
<b>MECHANICAL</b>					
w	Weight, typ	g	1000		
D <sub>s</sub>	Surface creepage distance	mm (inch)	36.50 (1.437)		
D <sub>a</sub>	Air strike distance	mm (inch)	16.5 (0.650)		

<b>PART NUMBERING GUIDE</b>				
DT	70	2000	18	
1	2	3	4	
1. DT - Phase Control Disc Thyristor				
2. Element Diameter				
3. Mean on-state current, A				
4. Voltage code				

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## OVERALL DIMENSIONS

Package type: T.E3



All dimensions in millimeters (inches)